

Fig. 2-46 SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 330, (b) 340, (c) 350, (d) 360 (e) 370 (f) 380 mJ/cm^2 . The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with UV exposure $\lambda 254\text{nm}$ for 600sec

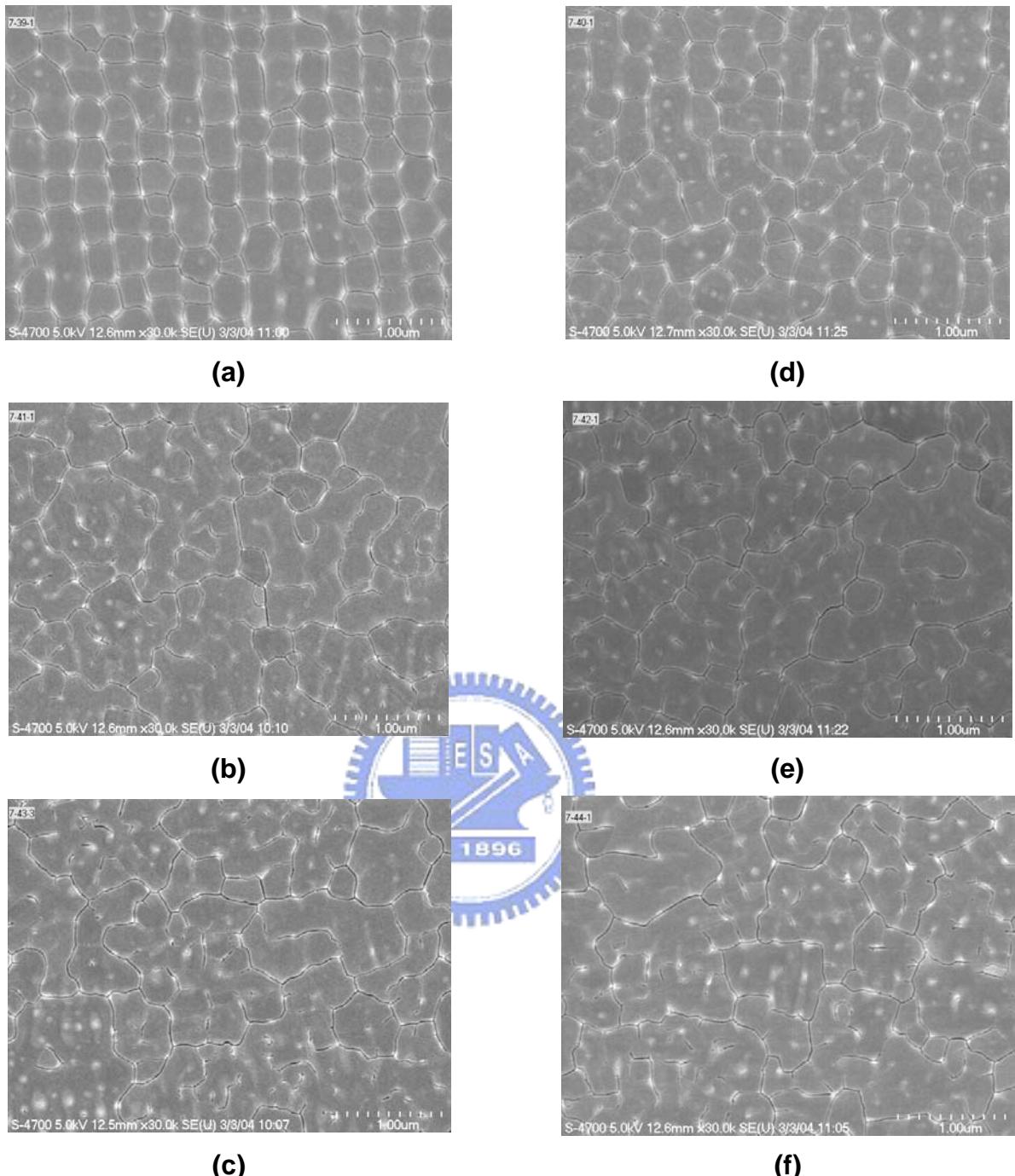


Fig. 2-47 SEM micrographs of excimer laser crystallized poly-Silicon films after Secco etching for 60sec treatment. The applied laser energy densities are (a) 390, (b) 400, (c) 410, (d) 420 (e) 430 (f) 440 mJ/cm². The laser energy 950mJ, frequency 300Hz, power 285W, scan speed 6mm/sec, pitch 0.02mm, beam width 0.4mm, pre treatment clean with UV exposure λ254nm for 600sec